

EH4745ETTS-75.000M



ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) LVCMOS (CMOS) 2.5Vdc 4 Pad 2.5mm x 3.2mm Ceramic Surface Mount (SMD)
 75.000MHz ± 50 ppm -40°C to +85°C

ELECTRICAL SPECIFICATIONS

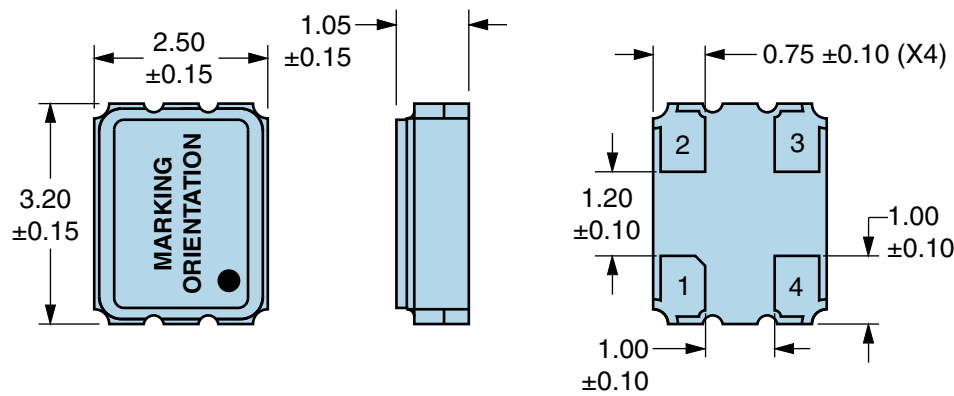
Nominal Frequency	75.000MHz
Frequency Tolerance/Stability	± 50 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, 260°C Reflow, Shock, and Vibration)
Aging at 25°C	± 5 ppm/Year Maximum
Operating Temperature Range	-40°C to +85°C
Supply Voltage	2.5Vdc $\pm 5\%$
Input Current	7mA Maximum (No Load)
Output Voltage Logic High (Voh)	90% of Vdd Minimum (IOH = -8mA)
Output Voltage Logic Low (Vol)	10% of Vdd Maximum (IOL = +8mA)
Rise/Fall Time	4nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 ± 5 (%) (Measured at 50% of waveform)
Load Drive Capability	15pF Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)
Standby Current	10 μ A Maximum (Pin 1 = Ground)
RMS Phase Jitter	20pSec Typical, 30pSec Maximum (Fj = 12kHz to 20MHz)
Period Jitter (RMS)	13pSec Typical
Period Jitter (pk-pk)	85pSec Typical, 100pSec Maximum
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500Vdc
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

EH4745ETTTTS-75.000M

MECHANICAL DIMENSIONS (all dimensions in millimeters)

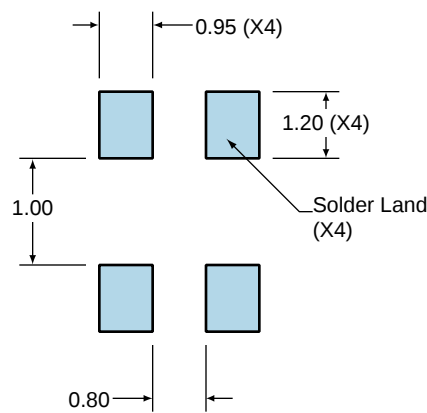


PIN	CONNECTION
1	Tri-State
2	Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	E75.000 <i>E=Ecliptek Designator</i>
2	XXXXXX <i>XXXXXX=Ecliptek Manufacturing Identifier</i>

Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1

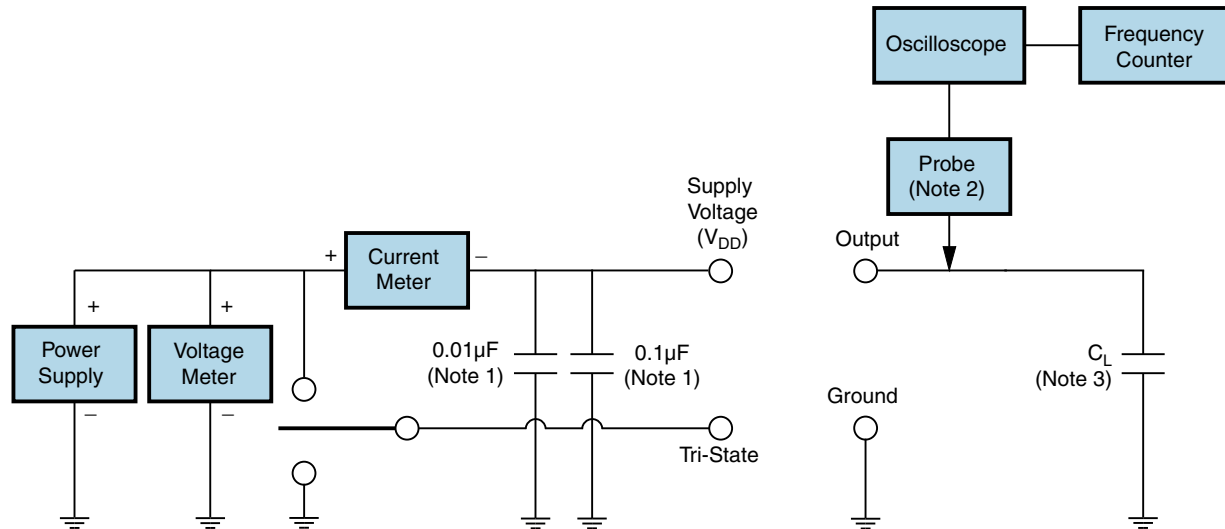
EH4745ETTTTS-75.000M

OUTPUT WAVEFORM & TIMING DIAGRAM



EH4745ETTS-75.000M [↗](#)

Test Circuit for CMOS Output



Note 1: An external 0.01μF ceramic bypass capacitor in parallel with a 0.1μF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

EH4745ETTS-75.000M [↗](#)

Recommended Solder Reflow Methods



High Temperature Infrared/Convection

T _S MAX to T _L (Ramp-up Rate)	3°C/Second Maximum
Preheat	
- Temperature Minimum (T _S MIN)	150°C
- Temperature Typical (T _S TYP)	175°C
- Temperature Maximum (T _S MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/Second Maximum
Time Maintained Above:	
- Temperature (T _L)	217°C
- Time (t _L)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t _p)	20 - 40 Seconds
Ramp-down Rate	6°C/Second Maximum
Time 25°C to Peak Temperature (t)	8 Minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

EH4745ETTS-75.000M [↗](#)

Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

TS MAX to TL (Ramp-up Rate)	5°C/Second Maximum
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Preheat

- Temperature Minimum (TS MIN)	N/A
- Temperature Typical (TS TYP)	150°C
- Temperature Maximum (TS MAX)	N/A
- Time (ts MIN)	60 - 120 Seconds

Ramp-up Rate (TL to TP)	5°C/Second Maximum
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Time Maintained Above:

- Temperature (TL)	150°C
- Time (tL)	200 Seconds Maximum

Peak Temperature (TP)	240°C Maximum
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Target Peak Temperature (TP Target)	240°C Maximum 2 Times / 230°C Maximum 1 Time
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Time within 5°C of actual peak (tp)	10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time
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Ramp-down Rate	5°C/Second Maximum
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Time 25°C to Peak Temperature (t)	N/A
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Moisture Sensitivity Level	Level 1
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Additional Notes	Temperatures shown are applied to body of device.
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Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)